

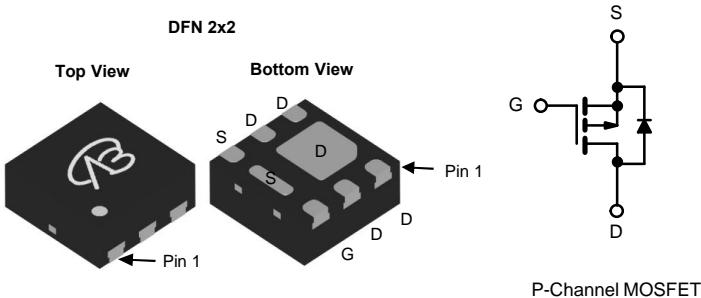
VBQG2216 Datasheet

P-Channel 20-V (D-S) MOSFET

| PRODUCT SUMMARY | | | |
|---------------------|------------------------------------|--------------------|-----------------------|
| V _{DS} (V) | R _{DS(on)} (Ω) | I _D (A) | Q _g (Typ.) |
| - 20 | 0.020 at V _{GS} = - 10 V | - 10 ^a | 20 nC |
| | 0.028 at V _{GS} = - 4.5 V | - 8 ^a | |
| | 0.040 at V _{GS} = - 2.5 V | - 6 | |

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Trench Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC



APPLICATIONS

- Portable Devices
 - Load Switch
 - Battery Switch
 - Charger Switch

| ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted | | | | |
|---|-----------------------------------|-----------------------|------|--|
| Parameter | Symbol | Limit | Unit | |
| Drain-Source Voltage | V _{DS} | - 20 | V | |
| Gate-Source Voltage | V _{GS} | ± 12 | | |
| Continuous Drain Current (T _J = 150 °C) | T _C = 25 °C | - 10 ^a | A | |
| | T _C = 70 °C | - 7 ^a | | |
| | T _A = 25 °C | - 8 ^{b, c} | | |
| | T _A = 70 °C | - 7.1 ^{b, c} | | |
| Pulsed Drain Current | I _{DM} | - 30 | | |
| Continuous Source-Drain Diode Current | T _C = 25 °C | - 6 ^a | W | |
| | T _A = 25 °C | - 2.9 ^{b, c} | | |
| Maximum Power Dissipation | T _C = 25 °C | 19 | W | |
| | T _C = 70 °C | 12 | | |
| | T _A = 25 °C | 3.5 ^{b, c} | | |
| | T _A = 70 °C | 2.2 ^{b, c} | | |
| Operating Junction and Storage Temperature Range | T _J , T _{stg} | - 55 to 150 | °C | |
| Soldering Recommendations (Peak Temperature) ^{d, e} | | 260 | | |

THERMAL RESISTANCE RATINGS

| Parameter | Symbol | Typical | Maximum | Unit |
|---|--------------|-------------------|---------|------|
| Maximum Junction-to-Ambient ^{b, e} | t ≤ 5 s | R _{thJA} | 28 | 36 |
| Maximum Junction-to-Case (Drain) | Steady State | R _{thJC} | 5.3 | 6.5 |

Notes:

- Package limited.
- Surface Mounted on 1" x 1" FR4 board.
- t = 5 s.
- Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under Steady State conditions is 80 °C/W.

SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted

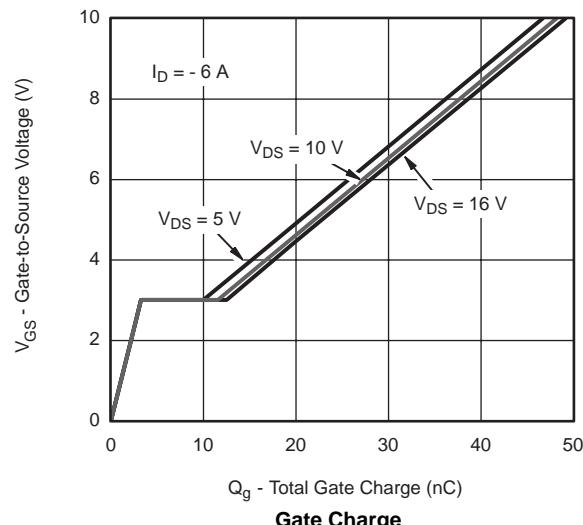
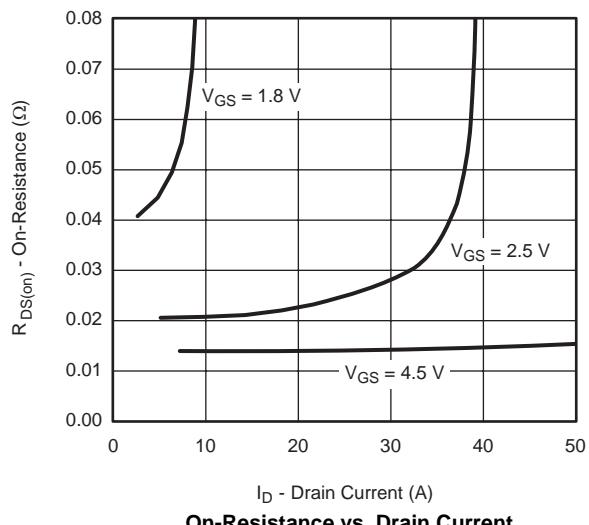
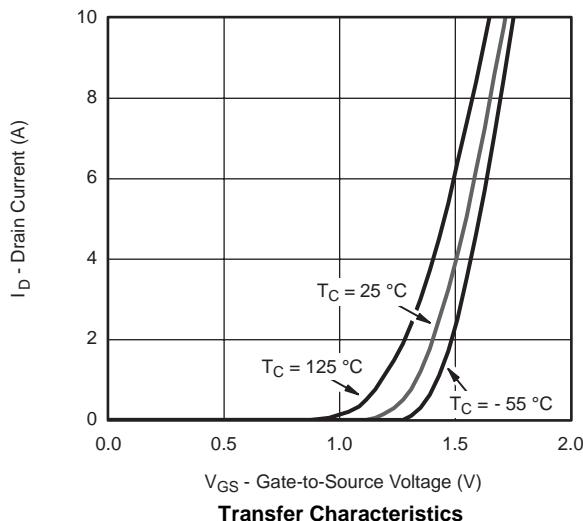
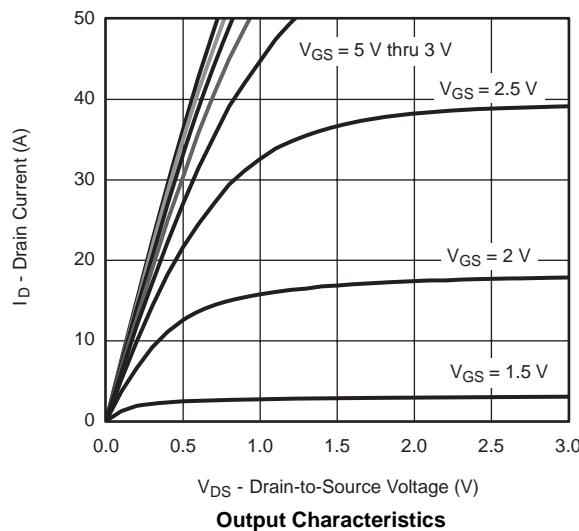
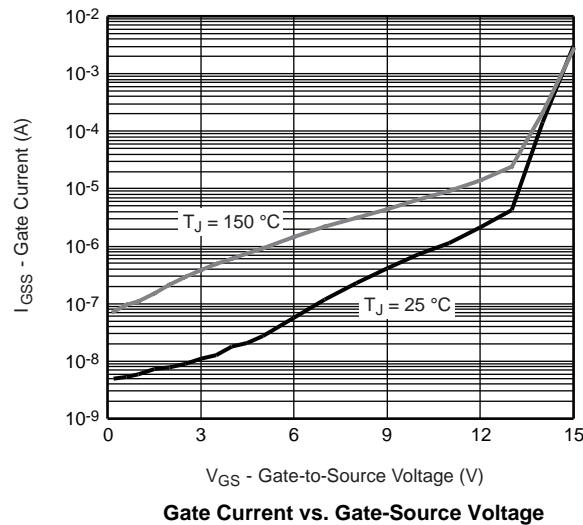
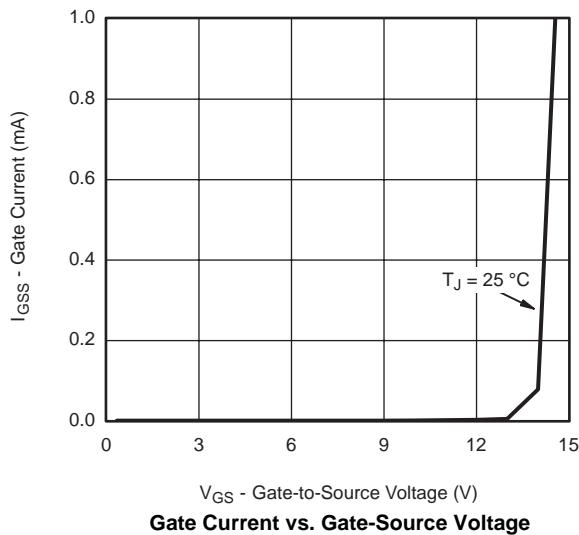
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
|--|--------------------------------|---|------|--------|-----------|---------------|
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$ | - 20 | | | V |
| V_{DS} Temperature Coefficient | $\Delta V_{DS}/T_J$ | $I_D = -250 \mu\text{A}$ | | - 12 | | mV/°C |
| $V_{GS(\text{th})}$ Temperature Coefficient | $\Delta V_{GS(\text{th})}/T_J$ | | | 3 | | |
| Gate-Source Threshold Voltage | $V_{GS(\text{th})}$ | $V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$ | | - 0.6 | | V |
| Gate-Source Leakage | I_{GSS} | $V_{DS} = -20 \text{ V}, V_{GS} = \pm 12 \text{ V}$ | | | ± 20 | μA |
| | | $V_{DS} = -20 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$ | | | ± 0.5 | |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$ | | | - 1 | |
| | | $V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^\circ\text{C}$ | | | - 10 | |
| On-State Drain Current ^a | $I_{D(\text{on})}$ | $V_{DS} \leq -5 \text{ V}, V_{GS} = -4.5 \text{ V}$ | - 20 | | | A |
| Drain-Source On-State Resistance ^a | $R_{DS(\text{on})}$ | $V_{GS} = -10 \text{ V}, I_D = -5.6 \text{ A}$ | | 0.020 | | Ω |
| | | $V_{GS} = -4.5 \text{ V}, I_D = -5.3 \text{ A}$ | | 0.028 | | |
| | | $V_{GS} = -2.5 \text{ V}, I_D = -2.5 \text{ A}$ | | 0.040 | | |
| Forward Transconductance ^a | g_{fs} | $V_{DS} = -10 \text{ V}, I_D = -5.6 \text{ A}$ | | 35 | | S |
| Dynamic^b | | | | | | |
| Total Gate Charge | Q_g | $V_{DS} = -10 \text{ V}, V_{GS} = -8 \text{ V}, I_D = -5 \text{ A}$ | | 50 | 75 | nC |
| Gate-Source Charge | Q_{gs} | $V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_D = -5 \text{ A}$ | | 20 | 30 | |
| | | | | 3.3 | | |
| Gate-Drain Charge | Q_{gd} | | | 8.4 | | |
| Gate Resistance | R_g | $f = 1 \text{ MHz}$ | 0.2 | 1 | 2 | k Ω |
| Turn-On Delay Time | $t_{d(\text{on})}$ | $V_{DD} = -10 \text{ V}, R_L = 1 \Omega$ $I_D \equiv -5 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$ | | 0.71 | 1.1 | us |
| Rise Time | t_r | | | 1.7 | 2.6 | |
| Turn-Off Delay Time | $t_{d(\text{off})}$ | | | 6 | 9 | |
| Fall Time | t_f | | | 3.2 | 5 | |
| Turn-On Delay Time | $t_{d(\text{on})}$ | $V_{DD} = -10 \text{ V}, R_L = 1 \Omega$ $I_D \equiv -5 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 1 \Omega$ | | 0.3 | 0.45 | |
| Rise Time | t_r | | | 0.6 | 0.9 | |
| Turn-Off Delay Time | $t_{d(\text{off})}$ | | | 10 | 15 | |
| Fall Time | t_f | | | 3.5 | 5.5 | |
| Drain-Source Body Diode Characteristics | | | | | | |
| Continuous Source-Drain Diode Current | I_S | $T_C = 25^\circ\text{C}$ | | | - 10 | A |
| Pulse Diode Forward Current | I_{SM} | | | | - 30 | |
| Body Diode Voltage | V_{SD} | $I_S = -5 \text{ A}, V_{GS} = 0 \text{ V}$ | | - 0.85 | - 1.2 | V |
| Body Diode Reverse Recovery Time | t_{rr} | $I_F = 6 \text{ A}, dI/dt = 100 \text{ A}/\mu\text{s}, T_J = 25^\circ\text{C}$ | | 30 | 60 | ns |
| Body Diode Reverse Recovery Charge | Q_{rr} | | | 20 | 40 | nC |
| Reverse Recovery Fall Time | t_a | | | 13 | | ns |
| Reverse Recovery Rise Time | t_b | | | 17 | | |

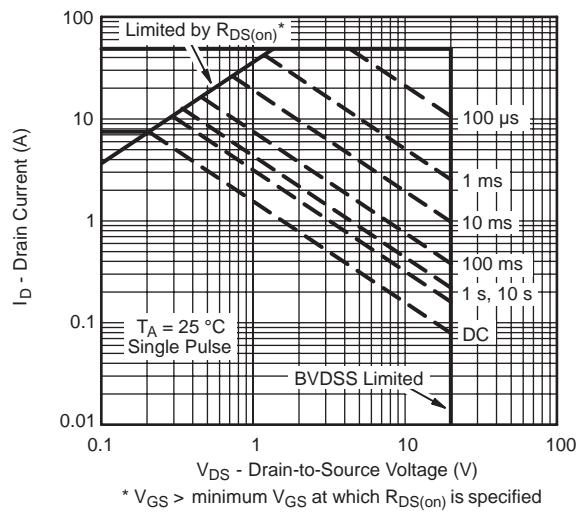
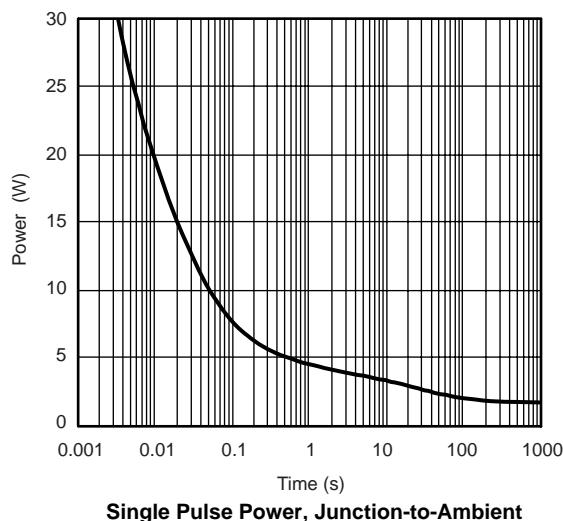
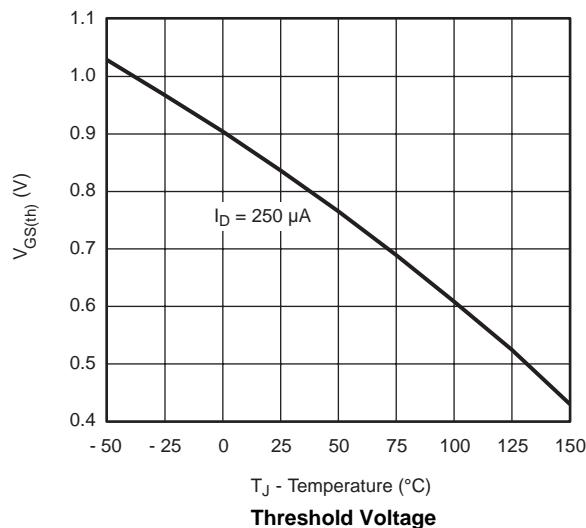
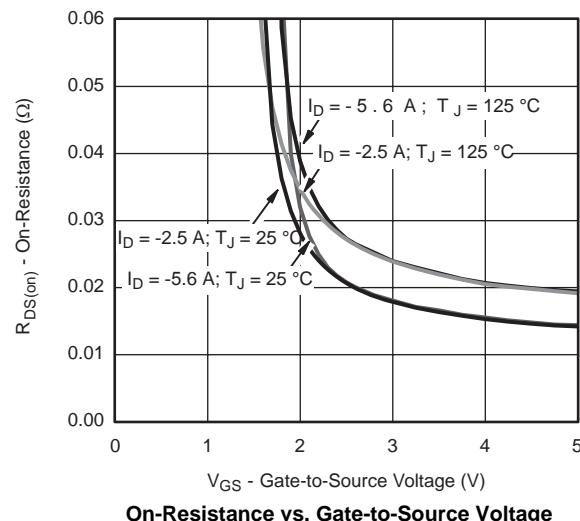
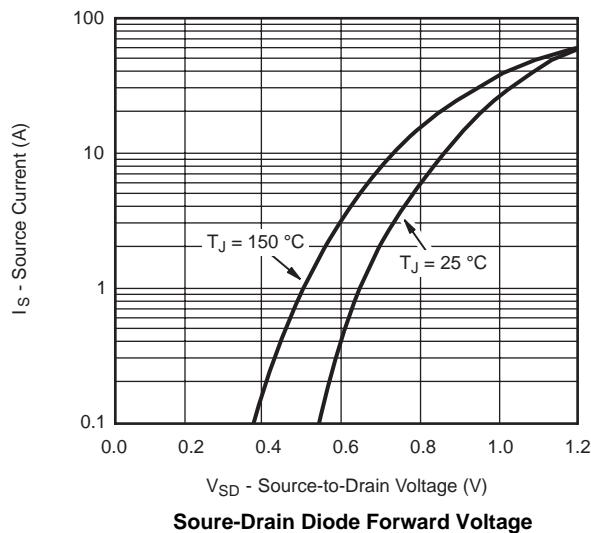
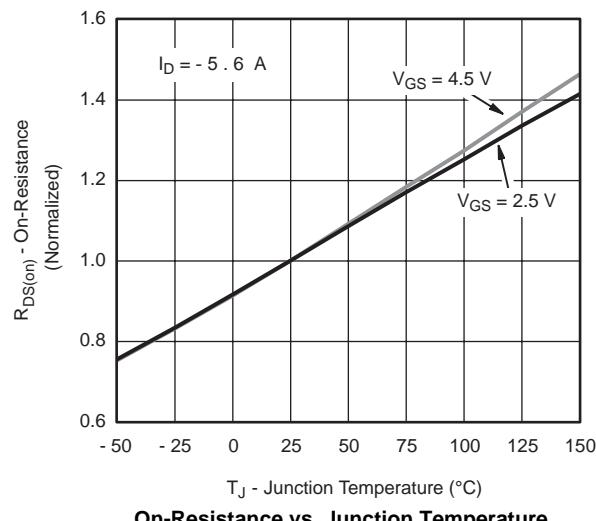
Notes:

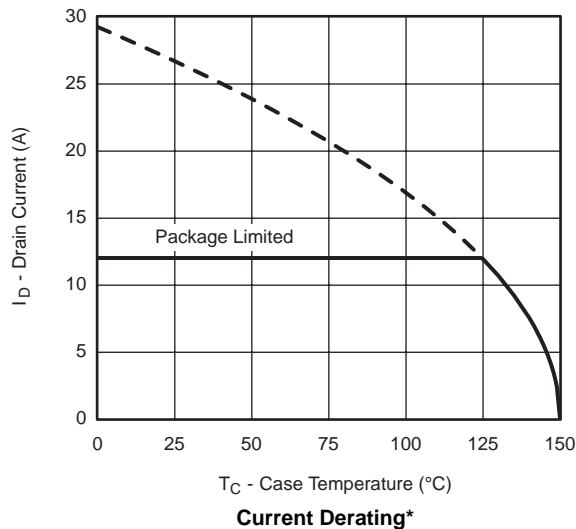
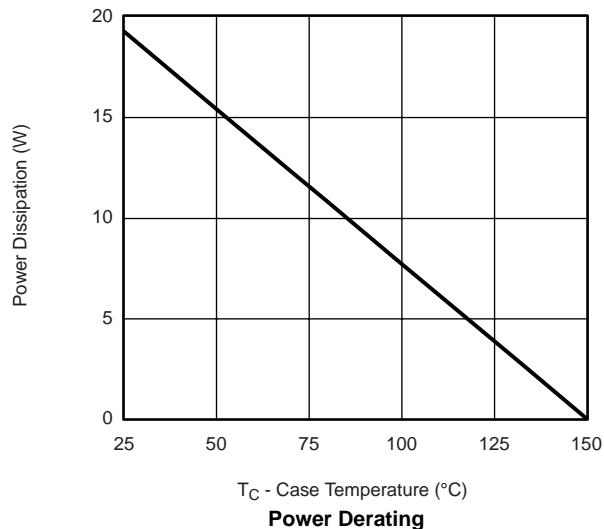
a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

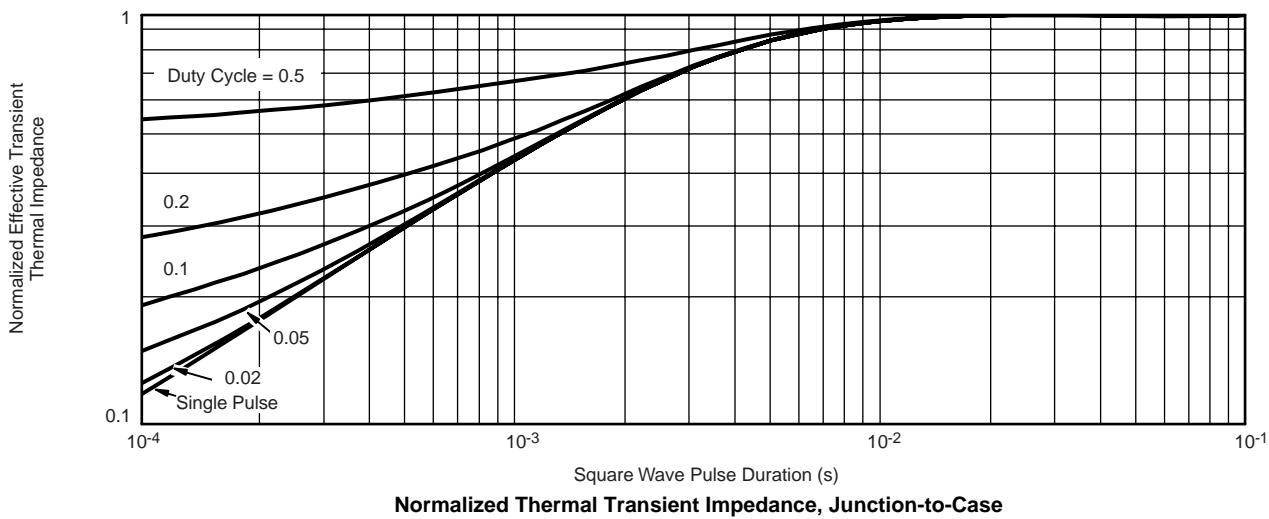
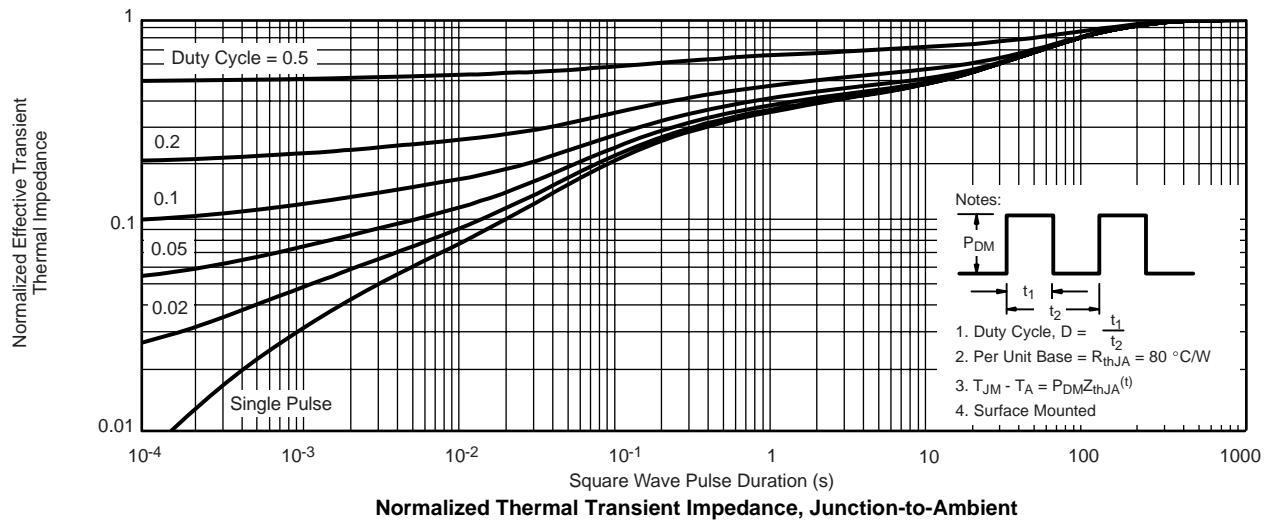
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


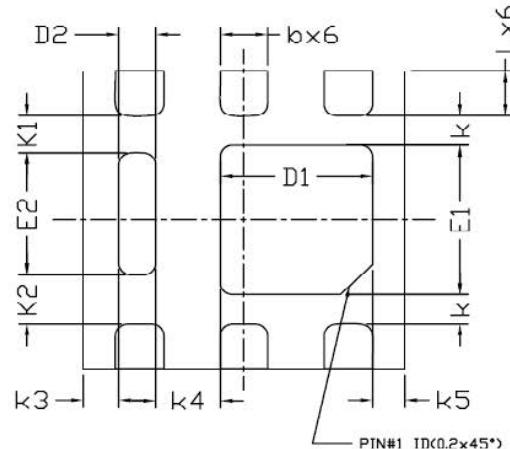
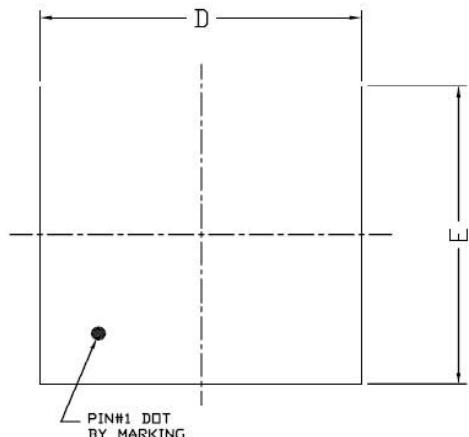
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Current Derating*****Power Derating**

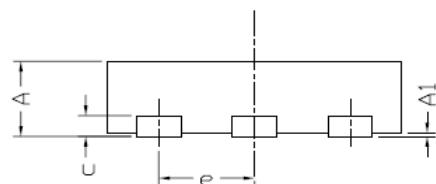
* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


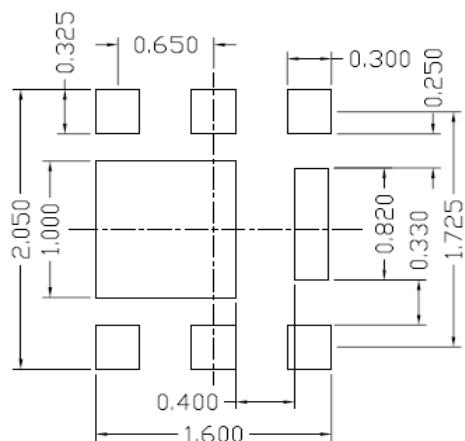
DFN2x2 _6L_EP1_S PACKAGE OUTLINE



BOTTOM VIEW



RECOMMENDED LAND PATTERN



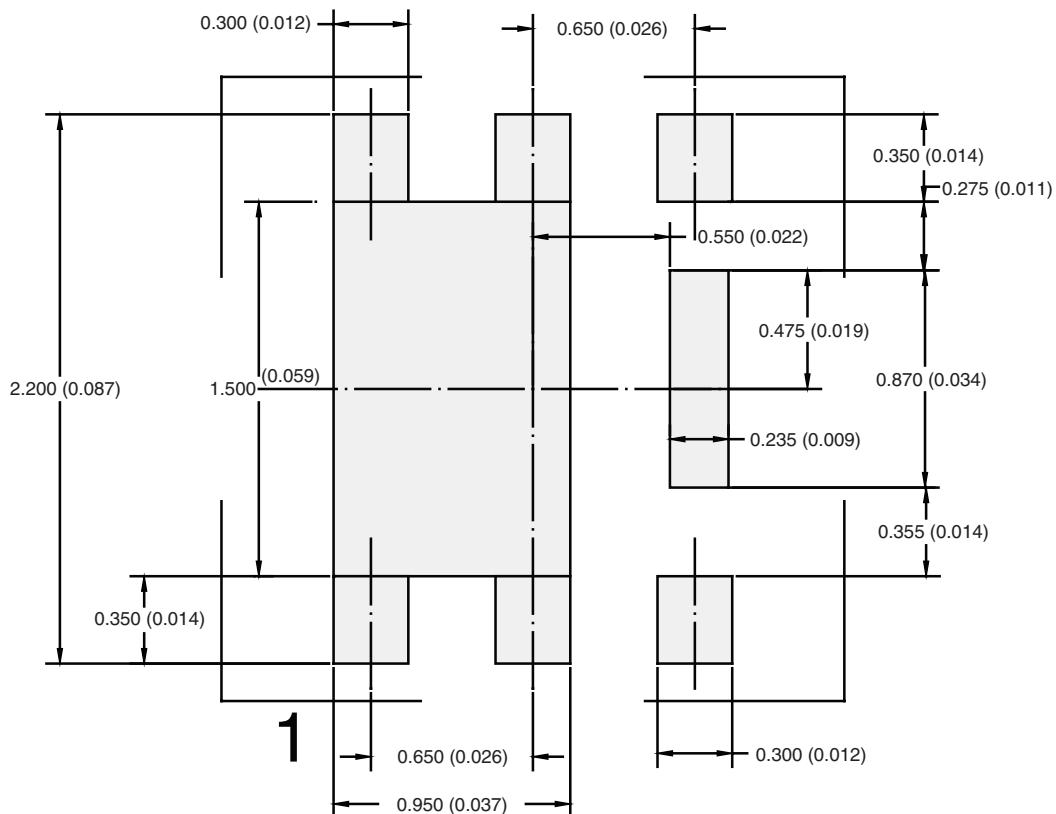
UNIT: mm

| SYMBOLS | DIMENSIONS IN MILLIMETERS | | | DIMENSIONS IN INCHES | | |
|---------|---------------------------|------|------|----------------------|-------|-------|
| | MIN | NOM | MAX | MIN | NOM | MAX |
| A | 0.50 | 0.55 | 0.60 | 0.020 | 0.022 | 0.024 |
| A1 | 0.00 | — | 0.05 | 0.000 | — | 0.002 |
| b | 0.25 | 0.30 | 0.35 | 0.010 | 0.012 | 0.014 |
| c | 0.152 REF | | | 0.006 REF | | |
| D | 1.90 | 2.00 | 2.10 | 0.075 | 0.079 | 0.083 |
| D1 | 0.85 | 0.95 | 1.05 | 0.033 | 0.037 | 0.041 |
| D2 | 0.13 | 0.23 | 0.33 | 0.005 | 0.009 | 0.013 |
| E | 1.90 | 2.00 | 2.10 | 0.075 | 0.079 | 0.083 |
| E1 | 0.90 | 1.00 | 1.10 | 0.035 | 0.039 | 0.043 |
| E2 | 0.72 | 0.82 | 0.92 | 0.028 | 0.032 | 0.036 |
| e | 0.65 BSC | | | 0.026 BSC | | |
| K | 0.20 BSC | | | 0.008 BSC | | |
| K1 | 0.25 BSC | | | 0.010 BSC | | |
| K2 | 0.33 BSC | | | 0.013 BSC | | |
| K3 | 0.22 BSC | | | 0.009 BSC | | |
| K4 | 0.40 BSC | | | 0.016 BSC | | |
| K5 | 0.20 BSC | | | 0.008 BSC | | |
| L | 0.25 | 0.30 | 0.35 | 0.010 | 0.012 | 0.014 |

NOTE

1. CONTROLLING DIMENSION IS MILLIMETER.
CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

RECOMMENDED PAD LAYOUT FOR DFN2X2



Dimensions in mm/(Inches)

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